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STD20NF20 STF20NF20, STP20NF20

N-channel 200 V, 0.10 Ω , 18 A DPAK, TO-220, TO-220FP
low gate charge STripFET™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D	P _W
STD20NF20	200 V	< 0.125 Ω	18 A	110 W
STF20NF20	200 V	< 0.125 Ω	18 A	30 W
STP20NF20	200 V	< 0.125 Ω	18 A	110 W

- Exceptional dv/dt capability
- Low gate charge
- 100% avalanche tested

Application

- Switching applications

Description

This Power MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters.

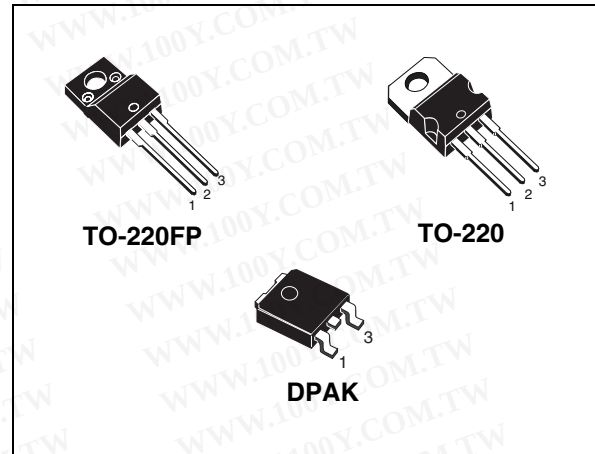


Figure 1. Internal schematic diagram

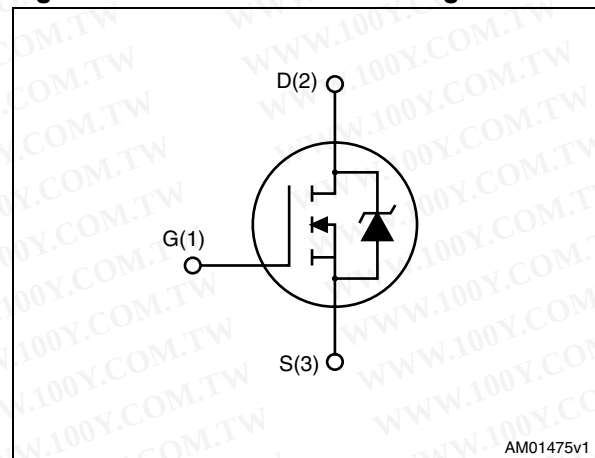


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD20NF20	20NF20	DPAK	Tape and reel
STF20NF20	20NF20	TO-220FP	Tube
STP20NF20	20NF20	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, DPAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	200		V
V_{GS}	Gate- source voltage	± 20		V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	18		A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	11		A
$I_{DM}^{(1)}$	Drain current (pulsed)	72		A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	110	30	W
	Derating factor	0.72	0.2	W/ $^{\circ}\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ }^{\circ}\text{C}$)		2500	V
T_{stg}	Storage temperature	-55 to 175		$^{\circ}\text{C}$
T_j	Max. operating junction temperature			

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 18\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	TO-220	DPAK	TO-220FP	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.38	1.38	5	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	50 ⁽¹⁾	62.5	$^{\circ}\text{C}/\text{W}$
T_I	Maximum lead temperature for soldering purpose			300	$^{\circ}\text{C}$

1. When mounted on 1inch² FR-4, 2 Oz copper board.

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	18	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	110	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	200			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$		0.10	0.125	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	$V_{DS} = 25\text{ V}$, $I_D = 10\text{ A}$	-	13		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	940 197 30		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 100\text{ V}$, $I_D = 10\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15)	-	15 30 40 10		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 160\text{ V}$, $I_D = 20\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 16)	-	28 5.6 14.5	39	nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		18 72	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 20\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 20\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$ (see Figure 20)	-	155 775 10		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 20\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$, $T_j = 150\text{ }^{\circ}\text{C}$ (see Figure 20)	-	183 1061 11.6		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, DPAK

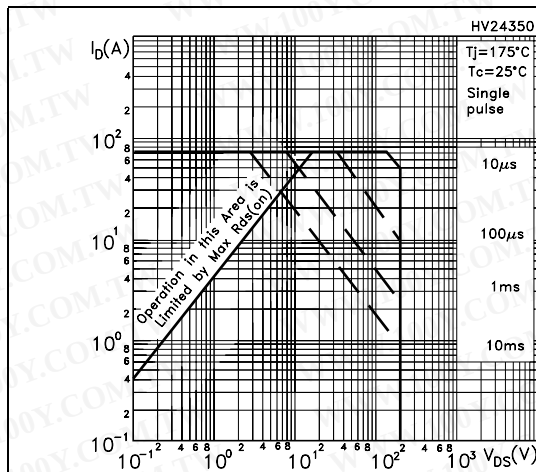


Figure 3. Thermal impedance area for TO-220, DPAK

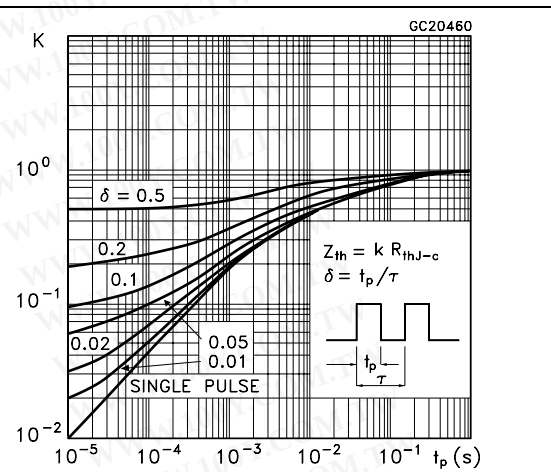


Figure 4. Safe operating area for TO-220FP

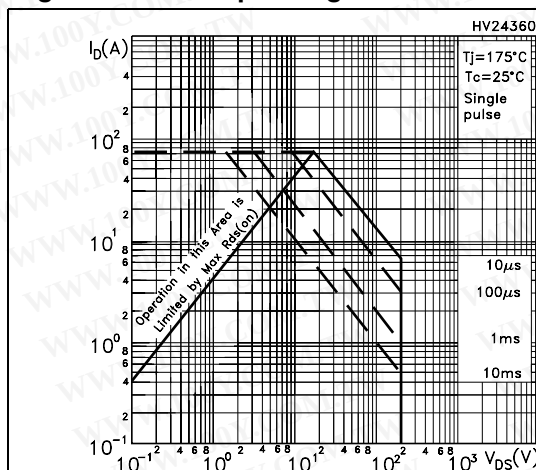


Figure 5. Thermal impedance for TO-220FP

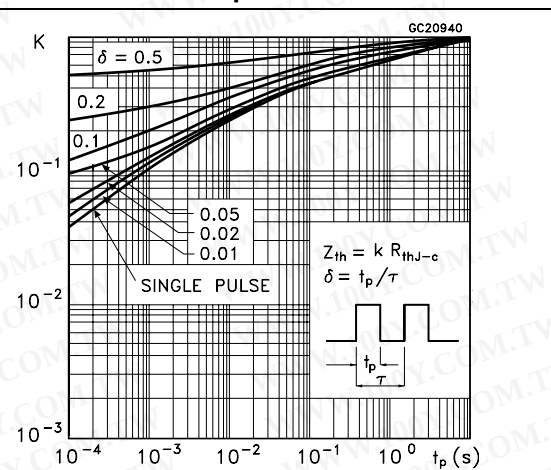


Figure 6. Output characteristics

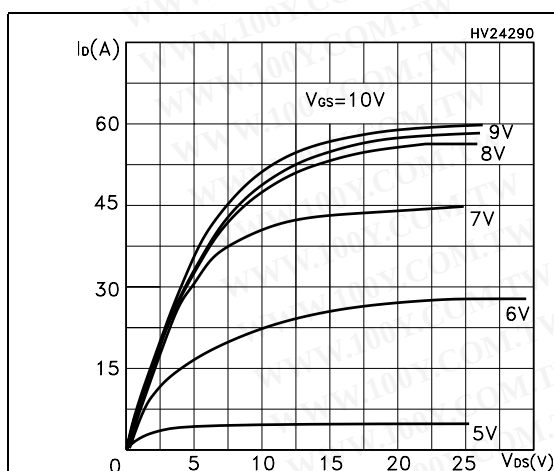


Figure 7. Transfer characteristics

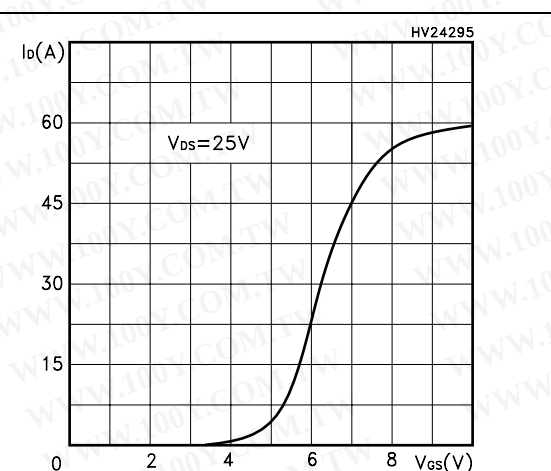


Figure 8. Transconductance

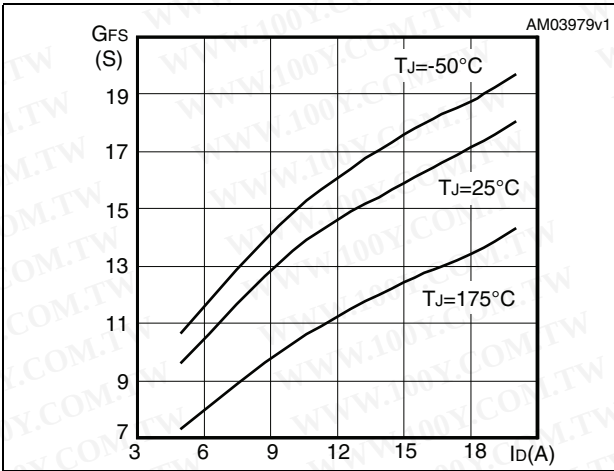


Figure 9. Static drain-source on resistance

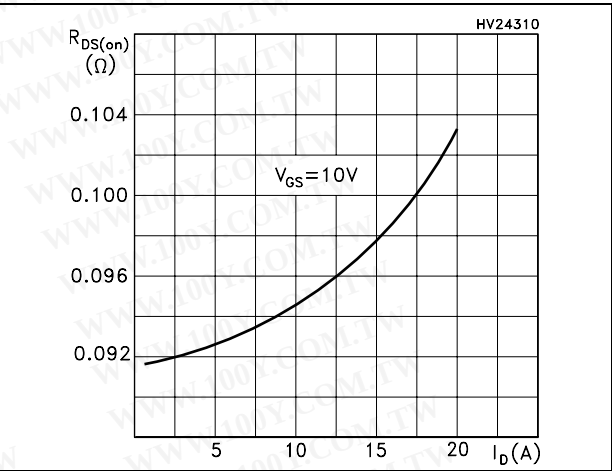


Figure 10. Gate charge vs gate-source voltage

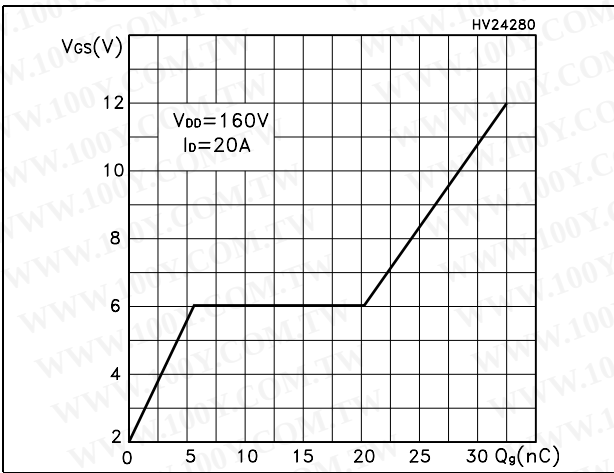


Figure 11. Capacitance variations

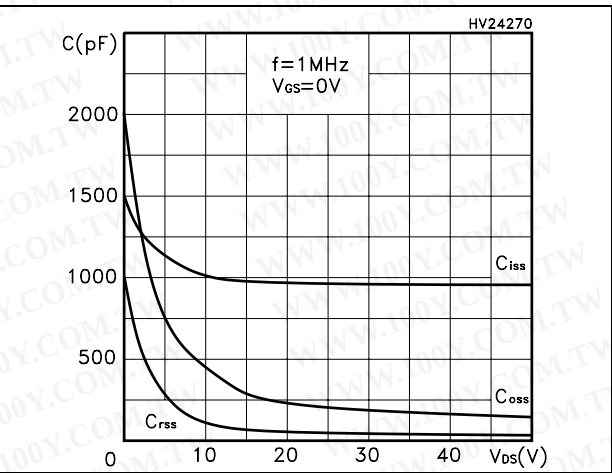


Figure 12. Normalized gate threshold voltage vs temperature

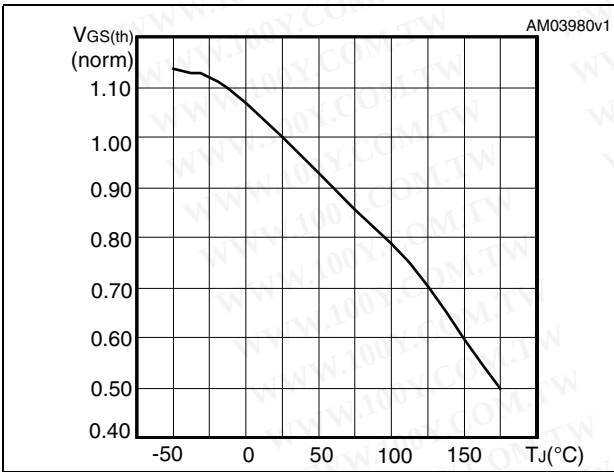


Figure 13. Normalized on resistance vs temperature

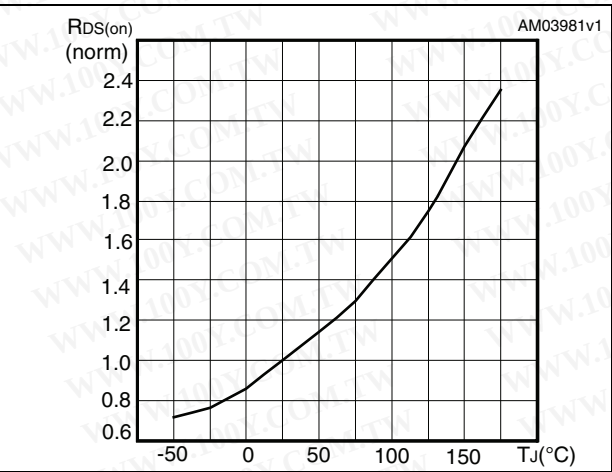
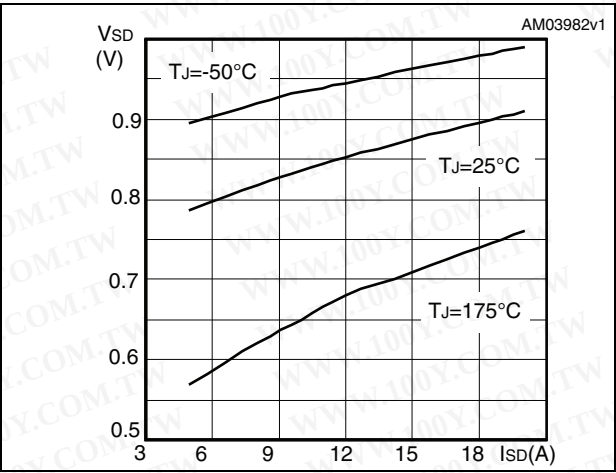


Figure 14. Source-drain diode forward characteristics



3 Test circuits

Figure 15. Switching times test circuit for resistive load

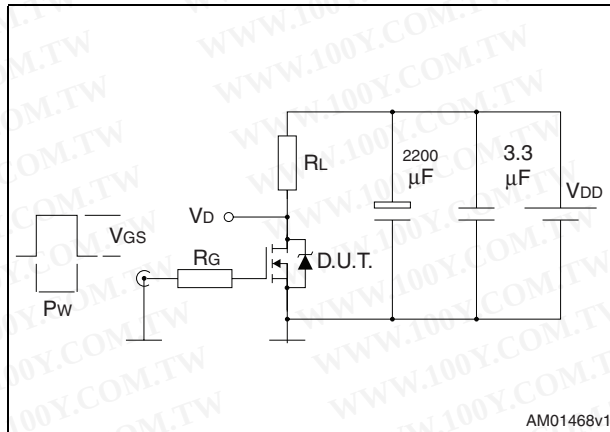


Figure 16. Gate charge test circuit

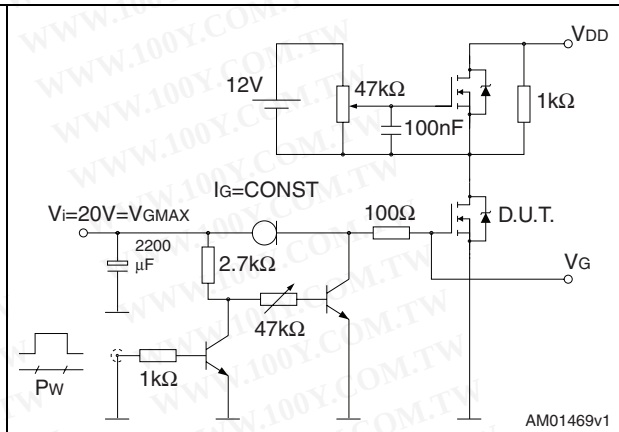


Figure 17. Test circuit for inductive load switching and diode recovery times

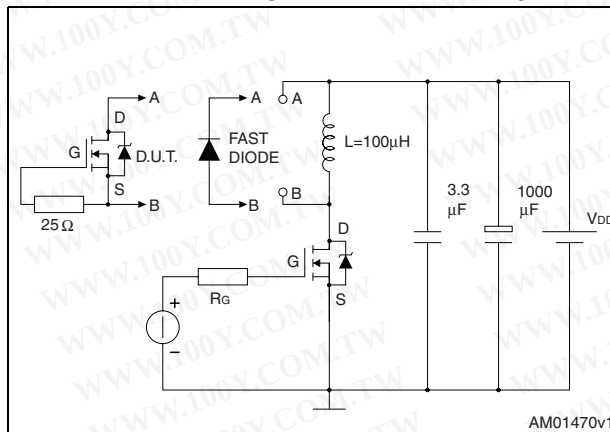


Figure 18. Unclamped inductive load test circuit

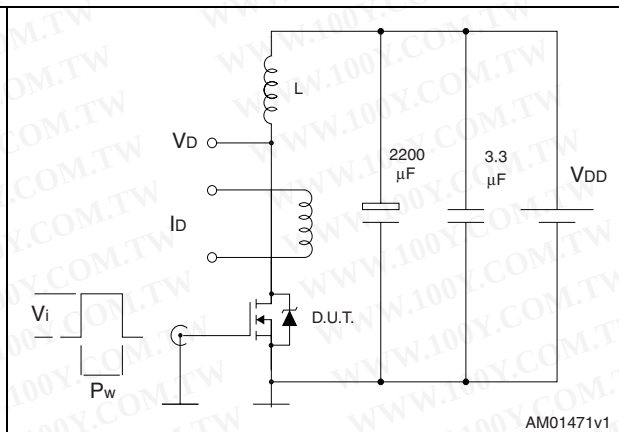


Figure 19. Unclamped inductive waveform

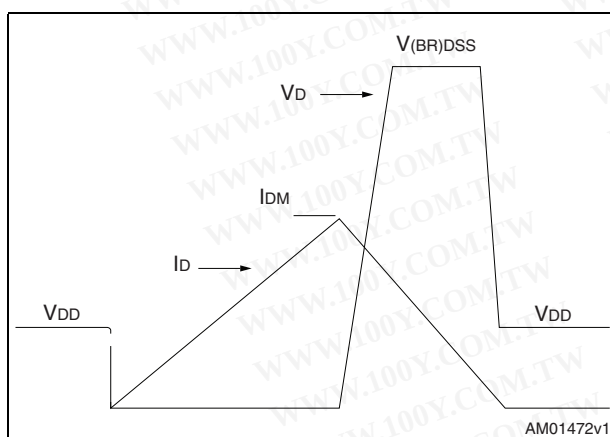
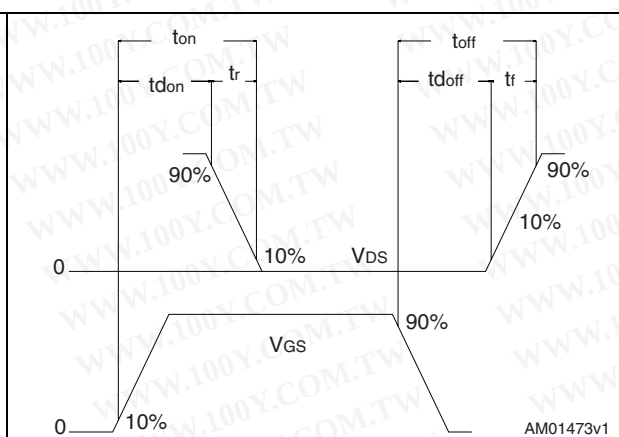


Figure 20. Switching time waveform

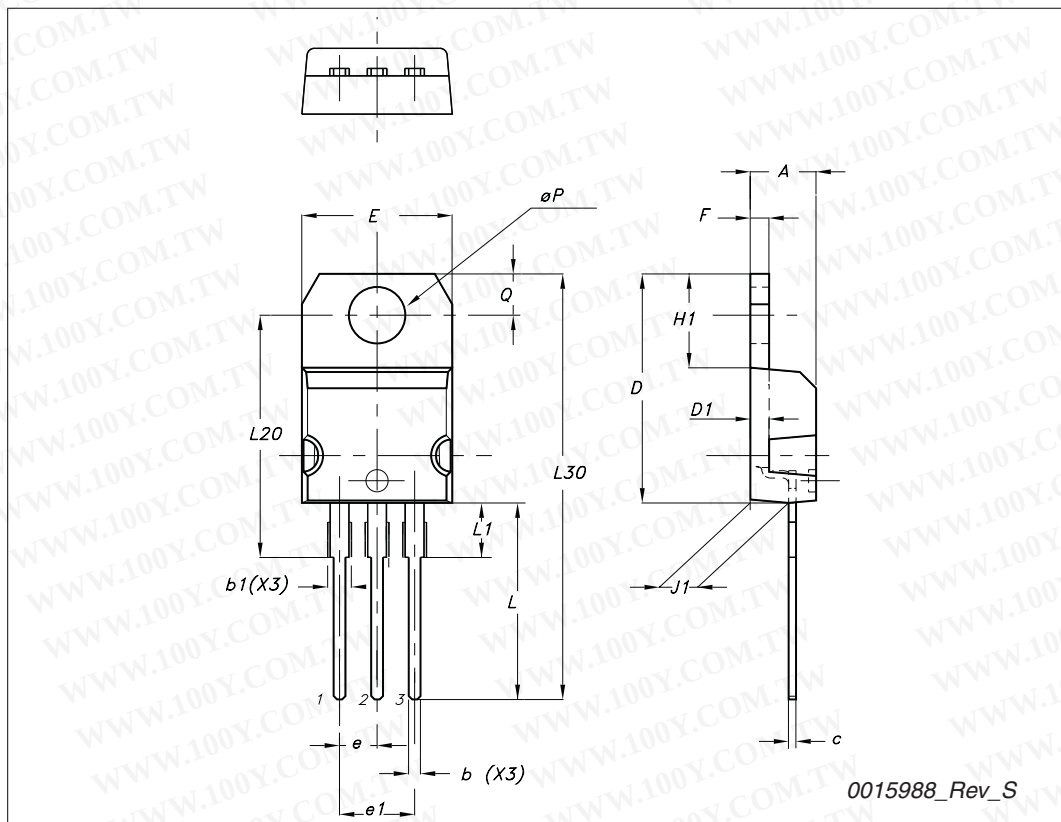


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

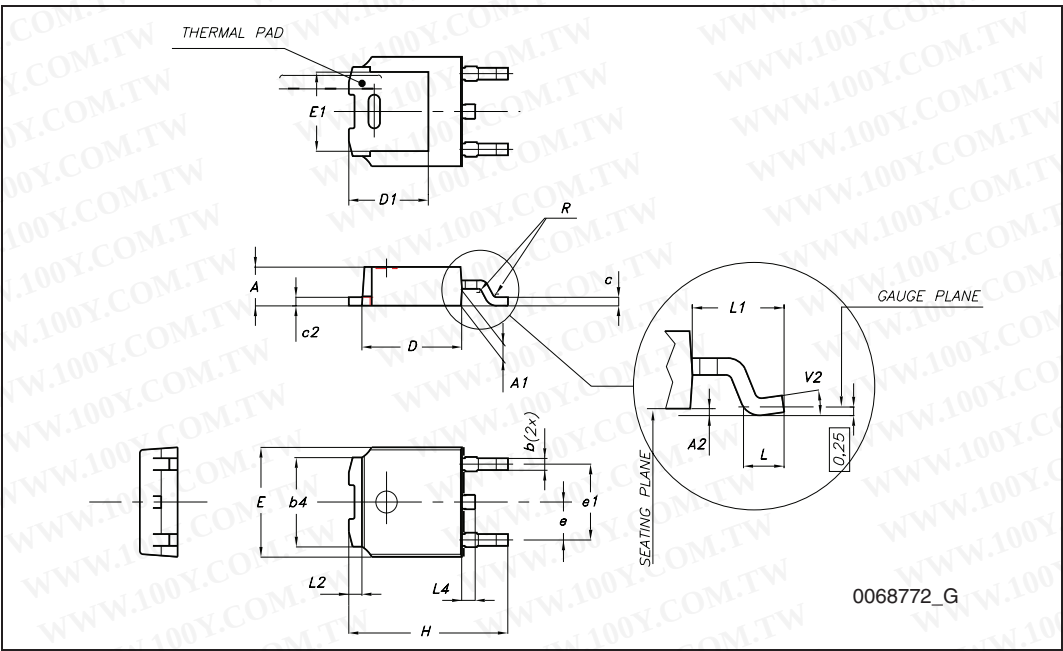
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



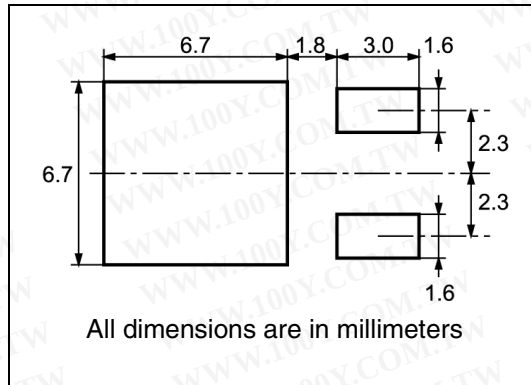
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °

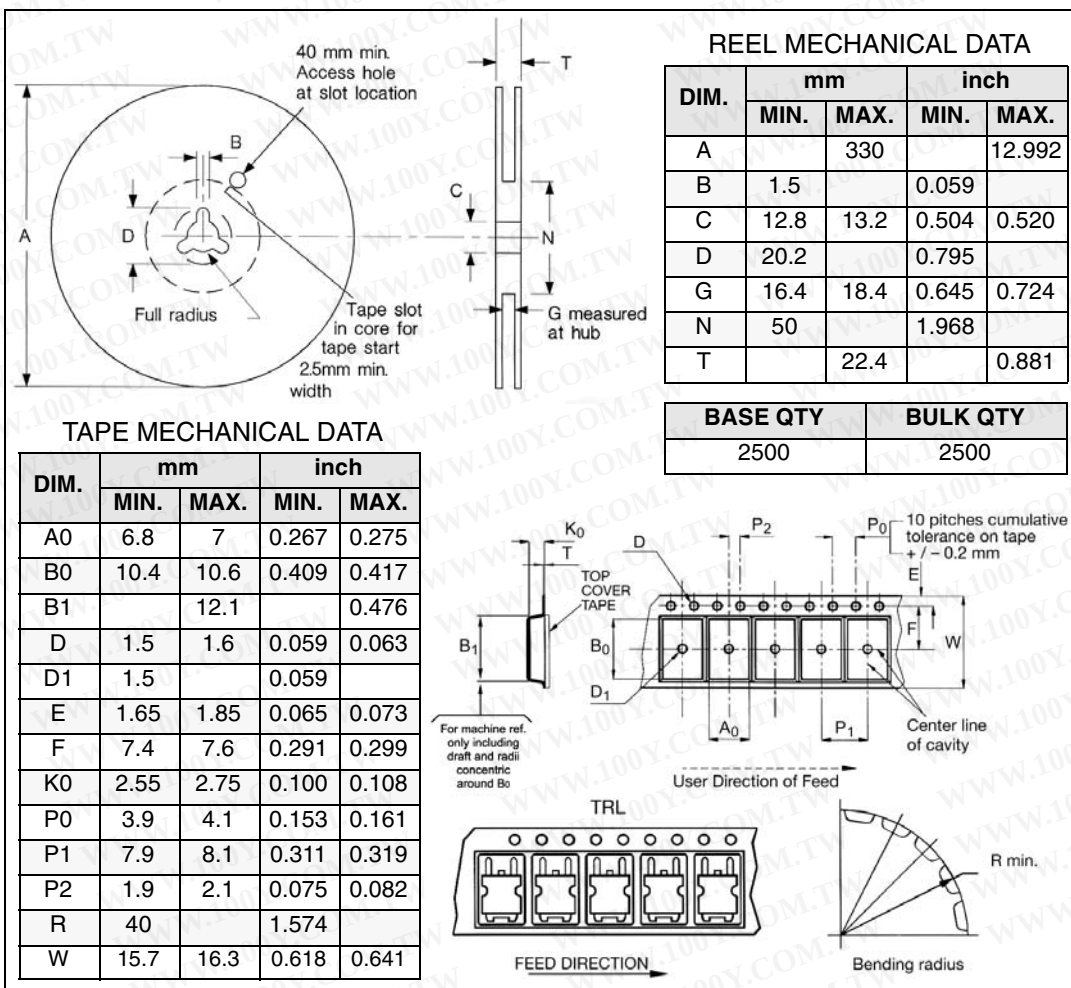


5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 8. Revision history

Date	Revision	Changes
25-Jan-2007	1	First release
20-Mar-2007	2	Typo mistake in first page (order codes)
27-Apr-2007	3	Updates on Table 6: Dynamic
10-Dec-2009	4	Modified device summary on first page

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